



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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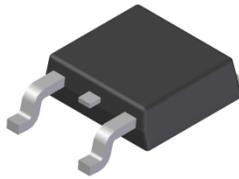
Features

- $BV_{CEO} > -32V$
- $I_C = -2A$ High Continuous Collector Current
- $I_{CM} = -3A$ Peak Pulse Current
- Epitaxial Planar Die Construction
- Low Collector-Emitter Saturation Voltage
- Ideal for Medium Power Switching or Amplification Applications

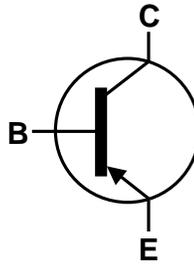
Mechanical Data

- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 
- Weight: 0.34 grams (Approximate)

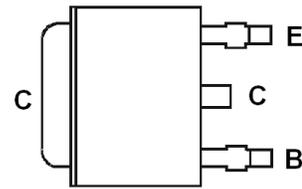
TO252 (DPAK)



Top View



Device Schematic



Pin Out Configuration
Top view

Absolute Maximum Ratings

 (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-32	V
Emitter-Base Voltage	V_{EBO}	-5	V
Continuous Collector Current	I_C	-2	A
Peak Pulse Collector Current	I_{CM}	-3	A

Thermal Characteristics

 (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation	P_D	1.2	W
Power Dissipation @ $T_L = +25^\circ\text{C}$	P_D	15	W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	104	$^\circ\text{C/W}$
Thermal Resistance, Junction to Lead	$R_{\theta JL}$	8.3	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

ESD Ratings

 (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Note:
- For a device mounted with the exposed collector pad on minimum recommended pad (MRP) layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
 - Thermal resistance from junction to solder-point (on the exposed collector pad).
 - Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics

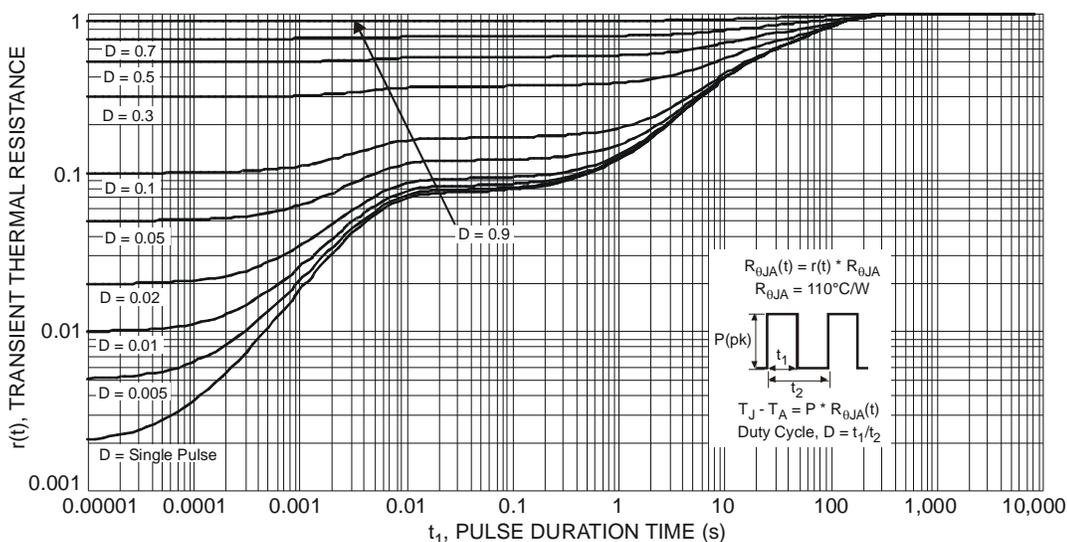


Figure 1 Transient Thermal Response

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Collector-Base Breakdown Voltage	BV_{CBO}	-40	—	—	V	$I_C = -50\mu\text{A}$, $I_E = 0$
Collector-Emitter Breakdown Voltage	BV_{CEO}	-32	—	—	V	$I_C = -1\text{mA}$, $I_B = 0$
Emitter-Base Breakdown Voltage	BV_{EBO}	-5	—	—	V	$I_E = -50\mu\text{A}$, $I_C = 0$
Collector Cutoff Current	I_{CBO}	—	—	-1	μA	$V_{CB} = -20\text{V}$, $I_E = 0$
Emitter Cutoff Current	I_{EBO}	—	—	-1	μA	$V_{EB} = -4\text{V}$, $I_C = 0$
ON CHARACTERISTICS (Note 8)						
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	—	—	-0.8	V	$I_C = -2\text{A}$, $I_B = -0.2\text{A}$
DC Current Gain	h_{FE}	120	—	270	—	$V_{CE} = -3\text{V}$, $I_C = -0.5\text{A}$
SMALL SIGNAL CHARACTERISTICS						
Current Gain-Bandwidth Product	f_T	—	110	—	MHz	$V_{CE} = -5\text{V}$, $I_C = -0.1\text{A}$, $f = 30\text{MHz}$
Output Capacitance	C_{obo}	—	26	—	pF	$V_{CB} = -10\text{V}$, $f = 1\text{MHz}$
Turn-On Time	t_{on}	—	109	—	ns	$V_{CC} = 30\text{V}$ $I_{CC} = 150\text{mA}$ $I_{B1} = -I_{B2} = 15\text{mA}$
Delay Time	t_d	—	60	—	ns	
Rise Time	t_r	—	49	—	ns	
Turn-Off Time	t_{off}	—	280	—	ns	
Storage Time	t_s	—	246	—	ns	
Fall Time	t_f	—	34	—	ns	

Note: 8. Measured under pulsed conditions. Pulse width = 300 μs . Duty cycle $\leq 2\%$.

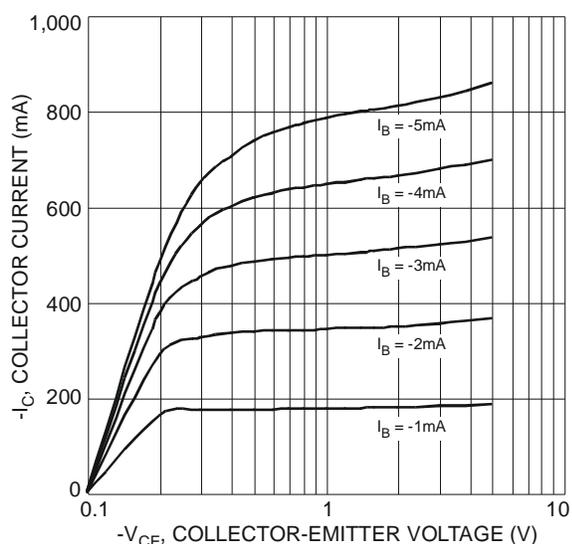
Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)


Figure 2 Typical Collector Current vs. Collector-Emitter Voltage

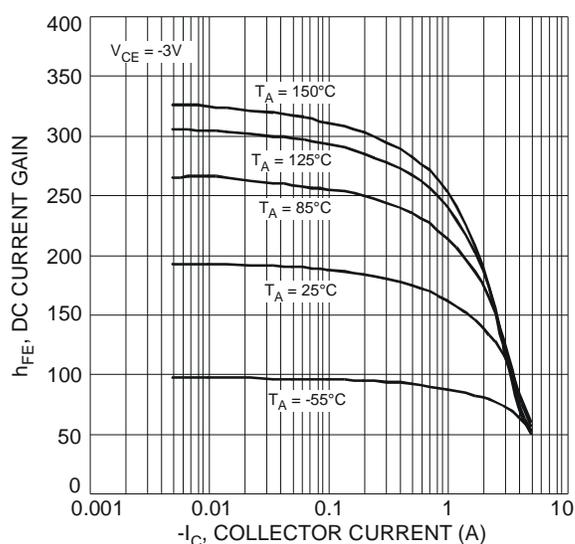


Figure 3 Typical DC Current Gain vs. Collector Current

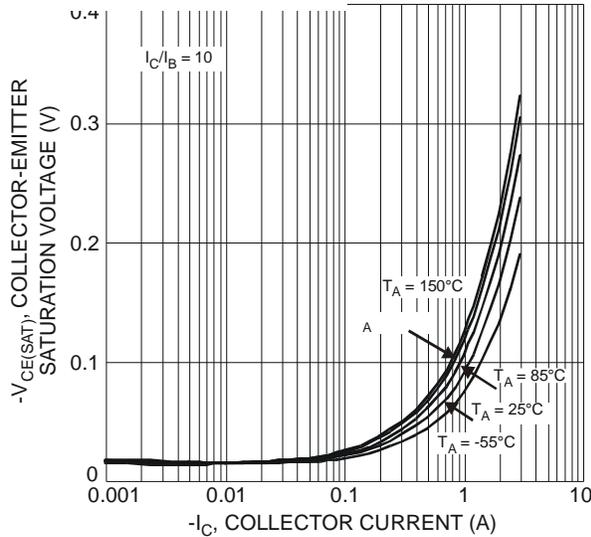


Figure 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

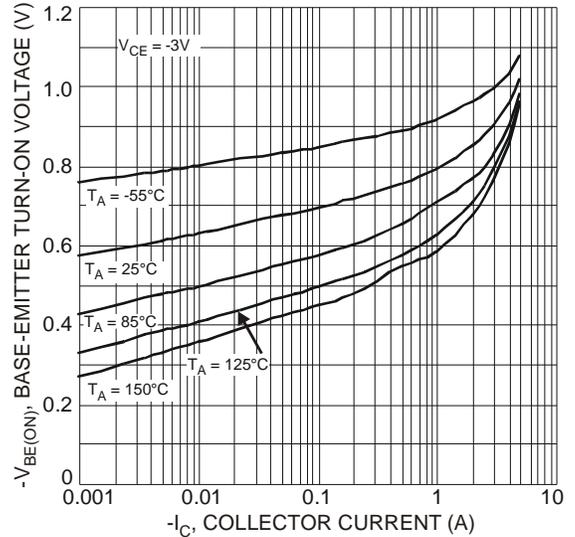


Figure 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current

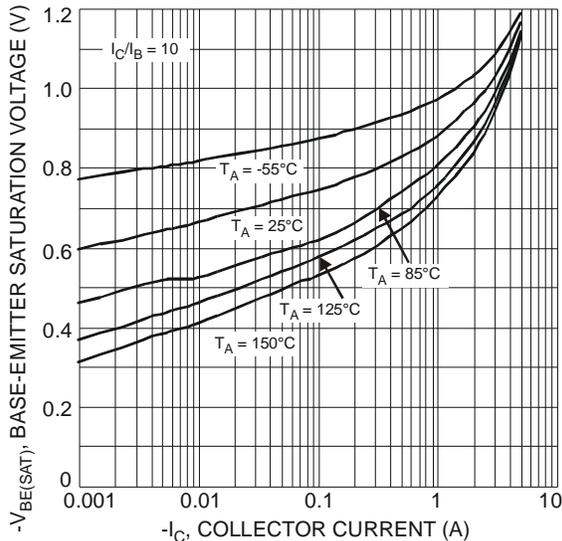


Figure 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

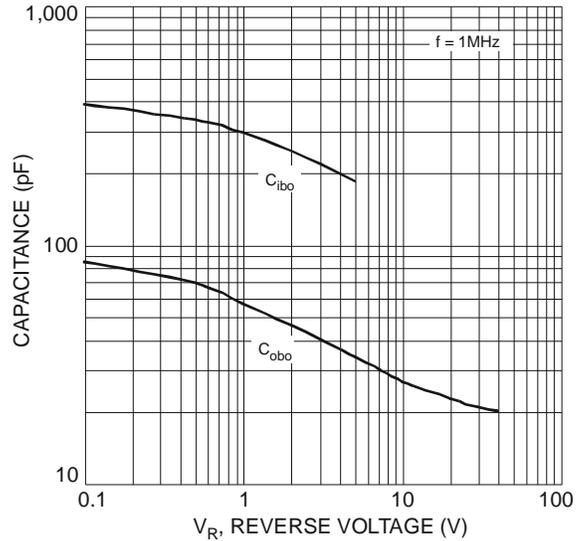


Figure 7 Typical Capacitance Characteristics

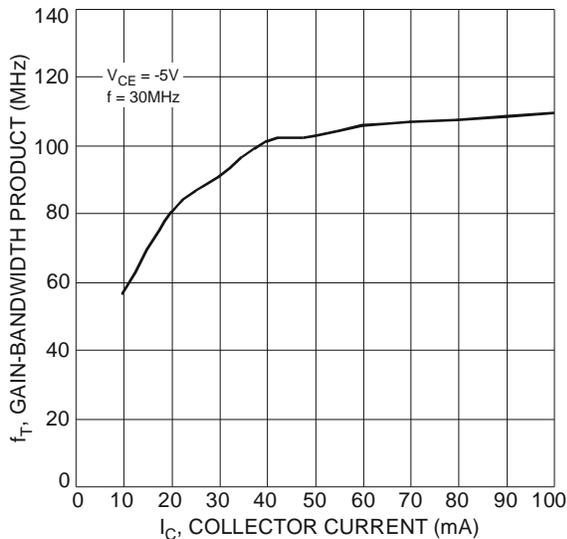
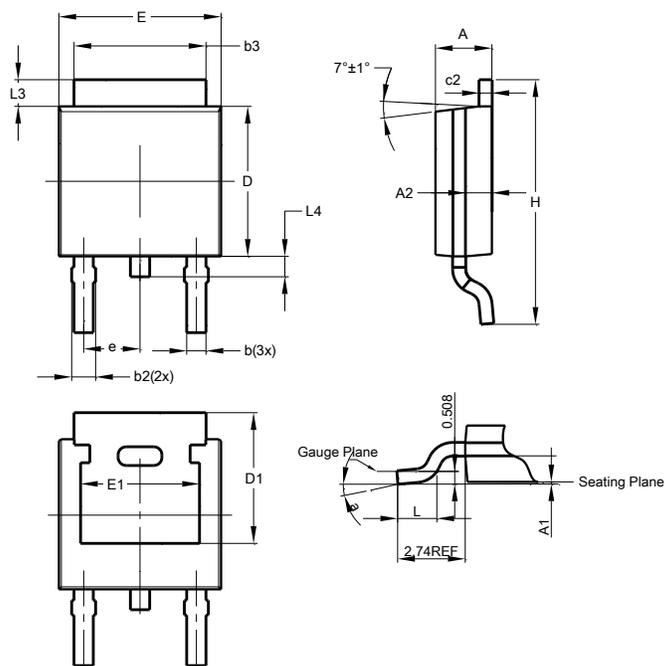


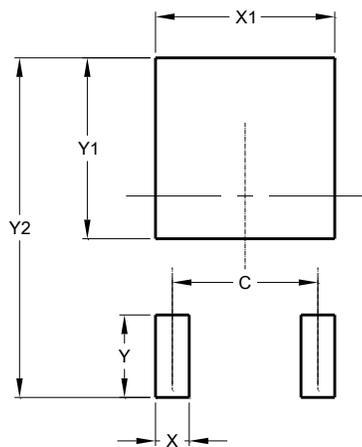
Figure 8 Typical Gain-Bandwidth Product vs. Collector Current

Package Outline Dimensions



TO252 (DPAK)			
Dim	Min	Max	Typ
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.46	5.33
c2	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	-	-
e	-	-	2.286
E	6.45	6.70	6.58
E1	4.32	-	-
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	-
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
C	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700